

# 2SC458, 2SC2308

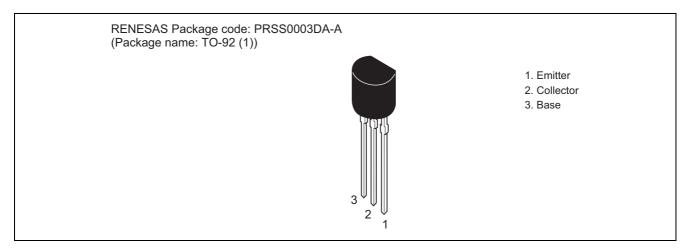
## Silicon NPN Epitaxial

REJ03G0681-0200 (Previous ADE-208-1043) Rev.2.00 Aug.10.2005

#### **Application**

- Low frequency amplifier
- Complementary pair with 2SA1029 and 2SA1030

#### **Outline**



### **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                         | Symbol           | 2SC458      | 2SC2308     | Unit |
|------------------------------|------------------|-------------|-------------|------|
| Collector to base voltage    | V <sub>CBO</sub> | 30          | 55          | V    |
| Collector to emitter voltage | V <sub>CEO</sub> | 30          | 50          | V    |
| Emitter to base voltage      | V <sub>EBO</sub> | 5           | 5           | V    |
| Collector current            | Ic               | 100         | 100         | mA   |
| Emitter current              | I <sub>E</sub>   | -100        | -100        | mA   |
| Collector power dissipation  | P <sub>C</sub>   | 200         | 200         | mW   |
| Junction temperature         | Tj               | 150         | 150         | °C   |
| Storage temperature          | Tstg             | -55 to +150 | -55 to +150 | °C   |

### **Electrical Characteristics**

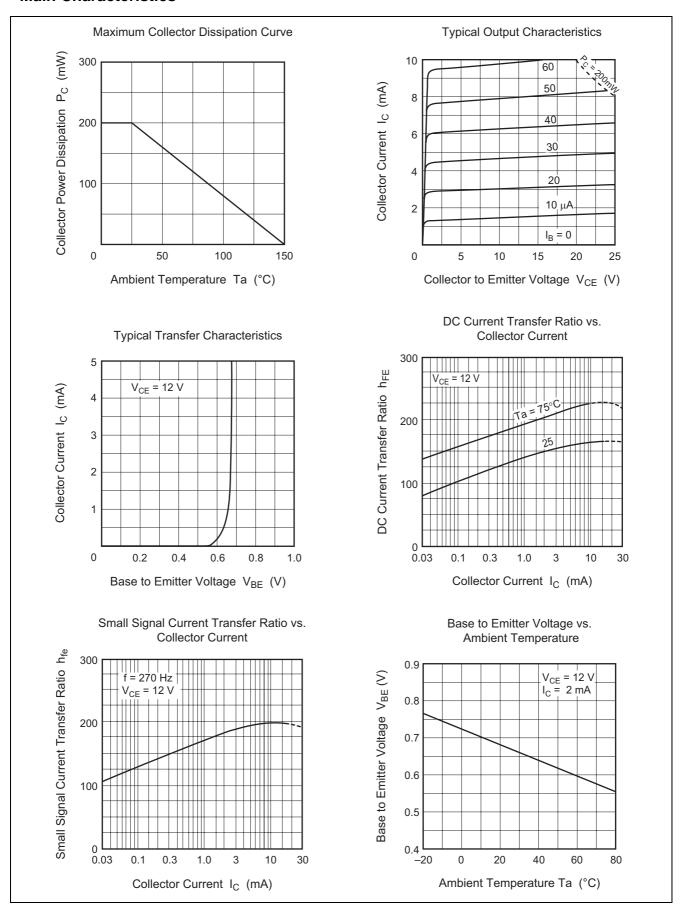
 $(Ta = 25^{\circ}C)$ 

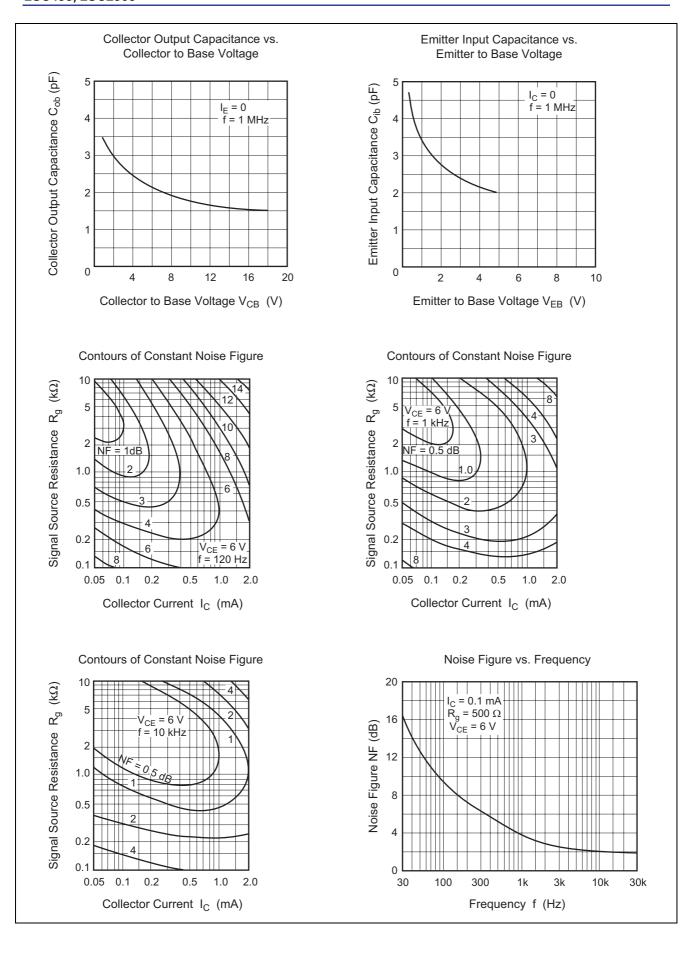
|   |                      |     | 2SC458 |      |     | 2SC2308 | 3    |                    |  |
|---|----------------------|-----|--------|------|-----|---------|------|--------------------|--|
| Item                                    | Symbol               | Min | Тур    | Max  | Min | Тур     | Max  | Unit               | Test conditions  |
| Collector to base breakdown voltage     | V <sub>(BR)CBO</sub> | 30  | _      | _    | 55  | _       | _    | V                  | $I_C = 10 \mu A, I_E = 0$  |
| Collector to emitter breakdown voltage  | V <sub>(BR)CEO</sub> | 30  | _      | _    | 50  | _       | _    | V                  | $I_C = 1 \text{ mA}, R_{BE} = \infty$  |
| Emitter to base breakdown voltage       | $V_{(BR)EBO}$        | 5   | _      | _    | 5   | _       | _    | V                  | $I_E = 10 \mu A, I_C = 0$  |
| Collector cutoff current                | I <sub>CBO</sub>     | _   | _      | 0.5  | _   | _       | 0.5  | μΑ                 | V <sub>CB</sub> =18 V, I <sub>E</sub> = 0  |
| Emitter cutoff current                  | I <sub>EBO</sub>     | _   | _      | 0.5  | _   | _       | 0.5  | μΑ                 | $V_{EB} = 2 \text{ V}, I_{C} = 0$  |
| DC current transfer ratio               | h <sub>FE</sub> *1   | 100 | _      | 500  | 160 | _       | 320  |                    | $V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$  |
| Collector to emitter saturation voltage | V <sub>CE(sat)</sub> | _   | _      | 0.2  | _   | _       | 0.2  | V                  | I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1 mA  |
| Base to emitter voltage                 | $V_{BE}$             | _   | 0.67   | 0.75 |     | 0.67    | 0.75 | V                  | $V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$  |
| Gain bandwidth product                  | f⊤                   | _   | 230    | _    | _   | 230     | _    | MHz                | $V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$  |
| Collector output capacitance            | Cob                  | _   | 1.8    | 3.5  | _   | 1.8     | 3.5  | pF                 | $V_{CB} = 10 \text{ V}, I_{E} = 0,$<br>f = 1 MHz   |
| Noise figure                            | NF                   | _   | 4      | 10   | _   | 4       | 10   | dB                 | $V_{CE} = 6 \text{ V}, I_{C} = 0.1 \text{ mA},$<br>$f = 1 \text{ kHz}, R_g = 500 \Omega$ |
| Small signal input impedance            | h <sub>ie</sub>      | _   | 16.5   | _    | _   | 16.5    | _    | kΩ                 | $V_{CE} = 5V, I_{C} = 0.1 \text{mA},$<br>f = 270 Hz                                      |
| Small signal voltage feedback ratio     | h <sub>re</sub>      | _   | 70     | _    | _   | 70      | _    | × 10 <sup>-6</sup> |  |
| Small signal current transfer ratio     | h <sub>fe</sub>      | _   | 130    | _    | _   | 130     | _    |                    |  |
| Small signal output admittance          | h <sub>oe</sub>      | _   | 11.0   | _    | _   | 11.0    | _    | μS                 |  |

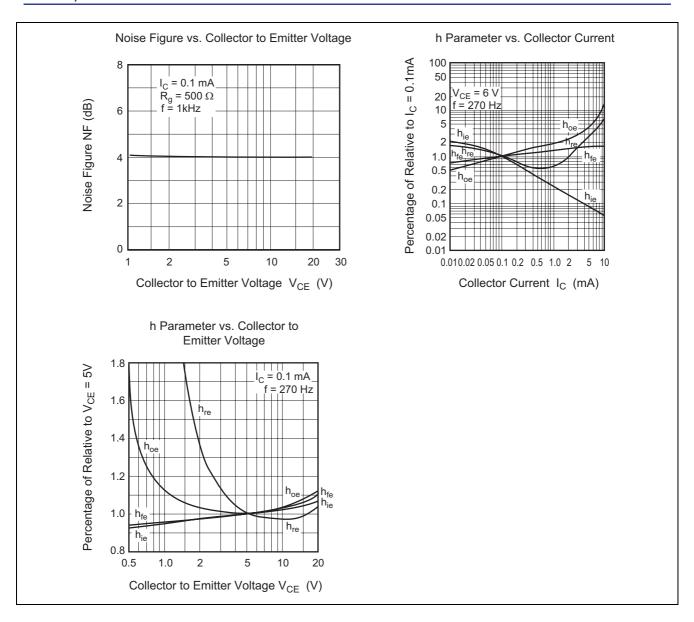
Note: 1. The 2SC458 is grouped by h<sub>FE</sub> as follows.

|        | В          | С          | D          |
|--------|------------|------------|------------|
| 2SC458 | 100 to 200 | 160 to 320 | 250 to 500 |

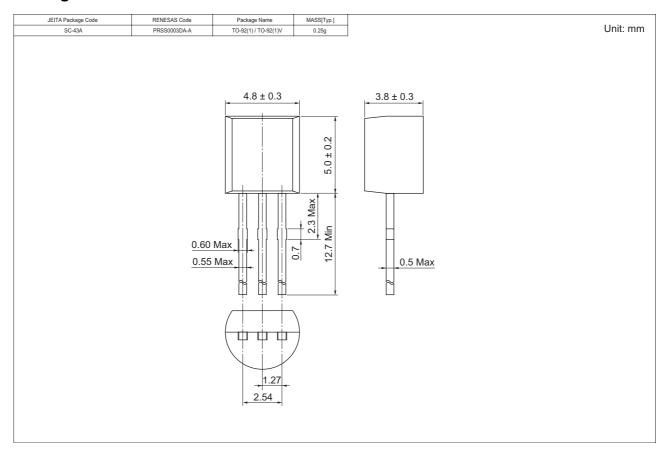
#### **Main Characteristics**







### **Package Dimensions**



### **Ordering Information**

| Part Name Quantity |      | Shipping Container      |  |  |
|--------------------|------|-------------------------|--|--|
| 2SC458BTZ          | 2500 | Hold Box, Radial Taping |  |  |
| 2SC458CTZ          |      |                         |  |  |
| 2SC458DTZ          |      |                         |  |  |
| 2SC2308CTZ         |      |                         |  |  |

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